Docket No.: 14467.05

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

John P. Snyder

nventor:

Application

10/796,514

No.:

Title:

Filing Date:

03/09/2004

TRANSISTOR HAVING HIGH DIELECTRIC

GATE INSULATING LAYER AND SOURCE

AND DRAIN FORMING SCHOTTKY CONTACT WITH SUBSTRATE

Confirmation No.:

1961

Examiner:

Kim, Su C

Group Art Unit:

2823

RESPONSE AFTER FINAL UNDER 37 C.F.R. 1.116

Mail Stop AF Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450 I hereby certify that this document is being sent via First Class U.S. mail addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 13 day of November, 2007.

Dear Sir:

Applicant hereby submits a response to the Final Office Action dated June 11, 2007.

Claims are reflected in the listing of claims which begins on page 2 of this paper. Claims 1, 15, 24, 33, 44 and 55 have been amended to patentably distinguish the present invention over the cited prior art.

Remarks/Arguments begin on page 11 of this paper.